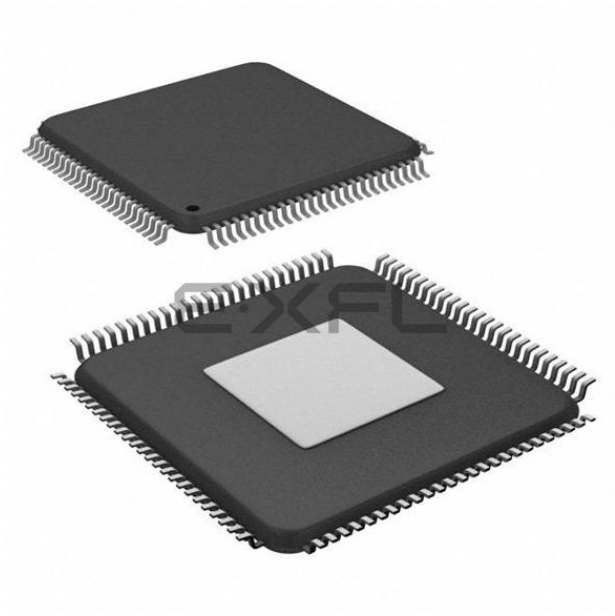
Infineon Technologies - XE164KN16F80LAAFXUMA1 Datasheet



Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	C166SV2
Core Size	16-Bit
Speed	80MHz
Connectivity	EBI/EMI, I²C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I²S, POR, PWM, WDT
Number of I/O	75
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	18K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 11x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-100-8
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xe164kn16f80laafxuma1

1.1 Device Types

The following XE164xN device types are available and can be ordered through Infineon's direct and/or distribution channels. The devices are available for the SAF temperature range. SAK types are available upon request only.

Table 1 Synopsis of XE164xN Device Types

Derivative	Flash Memory[1]	PSRAM DSRAM[2]	Capt./Comp. Modules	ADC[3] Chan.	Interfaces[3]
XE164FN-16F80L	128 Kbytes	8 Kbytes 8 Kbytes	CC2 CCU60/1	11 + 5	2 CAN Node, 6 Serial Chan.
XE164FN-24F80L	192 Kbytes	8 Kbytes 16 Kbytes	CC2 CCU60/1	11 + 5	2 CAN Node, 6 Serial Chan.
XE164FN-40F80L	320 Kbytes	16 Kbytes 16 Kbytes	CC2 CCU60/1	11 + 5	2 CAN Node, 6 Serial Chan.
XE164GN-16F80L	128 Kbytes	8 Kbytes 8 Kbytes	CC2 CCU60/1	6 + 5	2 CAN Node, 4 Serial Chan.
XE164GN-24F80L	192 Kbytes	8 Kbytes 16 Kbytes	CC2 CCU60/1	6 + 5	2 CAN Node, 4 Serial Chan.
XE164GN-40F80L	320 Kbytes	16 Kbytes 16 Kbytes	CC2 CCU60/1	6 + 5	2 CAN Node, 4 Serial Chan.
XE164HN-16F80L	128 Kbytes	8 Kbytes 8 Kbytes	CC2 CCU60/1	11 + 5	no CAN Nodes, 6 Serial Chan.
XE164HN-24F80L	192 Kbytes	8 Kbytes 16 Kbytes	CC2 CCU60/1	11 + 5	no CAN Nodes, 6 Serial Chan.
XE164HN-40F80L	320 Kbytes	16 Kbytes 16 Kbytes	CC2 CCU60/1	11 + 5	no CAN Nodes, 6 Serial Chan.
XE164KN-16F80L	128 Kbytes	8 Kbytes 8 Kbytes	CC2 CCU60/1	6 + 5	no CAN Nodes, 4 Serial Chan.
XE164KN-24F80L	192 Kbytes	8 Kbytes 16 Kbytes	CC2 CCU60/1	6 + 5	no CAN Nodes, 4 Serial Chan.
XE164KN-40F80L	320 Kbytes	16 Kbytes 16 Kbytes	CC2 CCU60/1	6 + 5	no CAN Nodes, 4 Serial Chan.

1) Specific information about the on-chip Flash memory in **Table 2**.

2) All derivatives additionally provide 8 Kbytes SBRAM and 2 Kbytes DPRAM.

3) Specific information about the available channels in **Table 4**.
Analog input channels are listed for each Analog/Digital Converter module separately (ADC0 + ADC1).

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
70	P10.5	O0 / I	St/B	**Bit 5 of Port 10, General Purpose Input/Output**
	U0C1_SCLKOUT	O1	St/B	**USIC0 Channel 1 Shift Clock Output**
	CCU60_COUT62	O2	St/B	**CCU60 Channel 2 Output**
	U2C0_DOUT	O3	St/B	**USIC2 Channel 0 Shift Data Output**
	AD5	OH / IH	St/B	**External Bus Interface Address/Data Line 5**
	U0C1_DX1B	I	St/B	**USIC0 Channel 1 Shift Clock Input**
71	P0.6	O0 / I	St/B	**Bit 6 of Port 0, General Purpose Input/Output**
	U1C1_DOUT	O1	St/B	**USIC1 Channel 1 Shift Data Output**
	TxDC1	O2	St/B	**CAN Node 1 Transmit Data Output**
	CCU61_COUT63	O3	St/B	**CCU61 Channel 3 Output**
	A6	OH	St/B	**External Bus Interface Address Line 6**
	U1C1_DX0A	I	St/B	**USIC1 Channel 1 Shift Data Input**
	CCU61_CTRAPA	I	St/B	**CCU61 Emergency Trap Input**
	U1C1_DX1B	I	St/B	**USIC1 Channel 1 Shift Clock Input**
72	P10.6	O0 / I	St/B	**Bit 6 of Port 10, General Purpose Input/Output**
	U0C0_DOUT	O1	St/B	**USIC0 Channel 0 Shift Data Output**
	U1C0_SELO0	O3	St/B	**USIC1 Channel 0 Select/Control 0 Output**
	AD6	OH / IH	St/B	**External Bus Interface Address/Data Line 6**
	U0C0_DX0C	I	St/B	**USIC0 Channel 0 Shift Data Input**
	U1C0_DX2D	I	St/B	**USIC1 Channel 0 Shift Control Input**
	CCU60_CTRAPA	I	St/B	**CCU60 Emergency Trap Input**

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
84	P1.2	O0 / I	St/B	**Bit 2 of Port 1, General Purpose Input/Output**
	U1C0_SELO 6	O2	St/B	**USIC1 Channel 0 Select/Control 6 Output**
	U2C1_SCLK OUT	O3	St/B	**USIC2 Channel 1 Shift Clock Output**
	A10	OH	St/B	**External Bus Interface Address Line 10**
	ESR1_4	I	St/B	**ESR1 Trigger Input 4**
	CCU61_T12 HRB	I	St/B	**External Run Control Input for T12 of CCU61**
	U2C1_DX0D	I	St/B	**USIC2 Channel 1 Shift Data Input**
	U2C1_DX1C	I	St/B	**USIC2 Channel 1 Shift Clock Input**
85	P10.12	O0 / I	St/B	**Bit 12 of Port 10, General Purpose Input/Output**
	U1C0_DOUT	O1	St/B	**USIC1 Channel 0 Shift Data Output**
	TDO_B	OH / IH	St/B	**JTAG Test Data Output / DAP1 Input/Output** If DAP pos. 1 is selected during start-up, an internal pull-down device will hold this pin low when nothing is driving it.
	AD12	OH / IH	St/B	**External Bus Interface Address/Data Line 12**
	U1C0_DX0C	I	St/B	**USIC1 Channel 0 Shift Data Input**
	U1C0_DX1E	I	St/B	**USIC1 Channel 0 Shift Clock Input**
86	P10.13	O0 / I	St/B	**Bit 13 of Port 10, General Purpose Input/Output**
	U1C0_DOUT	O1	St/B	**USIC1 Channel 0 Shift Data Output**
	U1C0_SELO 3	O3	St/B	**USIC1 Channel 0 Select/Control 3 Output**
	$\overline{WR}$/$\overline{WRL}$	OH	St/B	**External Bus Interface Write Strobe Output** Active for each external write access, when $\overline{WR}$, active for ext. writes to the low byte, when $\overline{WRL}$.
	U1C0_DX0D	I	St/B	**USIC1 Channel 0 Shift Data Input**

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
2, 25, 27, 50, 52, 75, 77, 100	V_{DDPB}	-	PS/B	**Digital Pad Supply Voltage for Domain B** Connect decoupling capacitors to adjacent V_{DDP}/V_{SS} pin pairs as close as possible to the pins. *Note: The on-chip voltage regulators and all ports except P5, P6 and P15 are fed from supply voltage V_{DDPB}.*
1, 26, 51, 76	V_{SS}	-	PS/--	**Digital Ground** All V_{SS} pins must be connected to the ground-line or ground-plane. *Note: Also the exposed pad is connected internally to V_{SS}. To improve the EMC behavior, it is recommended to connect the exposed pad to the board ground. For thermal aspects, please refer to the Data Sheet. Board layout examples are given in an application note.*

1) To generate the reference clock output for bus timing measurement, f_{SYS} must be selected as source for EXTCLK and P2.8 must be selected as output pin. Also the high-speed clock pad must be enabled. This configuration is referred to as reference clock output signal CLKOUT.

2.2 Identification Registers

The identification registers describe the current version of the XE164xN and of its modules.

Table 6 XE164xN Identification Registers

Short Name	Value	Address	Notes
SCU_IDMANUF	1820_H	$00'F07E_H$	
SCU_IDCHIP	3001_H	$00'F07C_H$	marking EES-AA or ES-AA
	3002_H	$00'F07C_H$	marking AA, AB
SCU_IDMEM	$304F_H$	$00'F07A_H$	
SCU_IDPROG	1313_H	$00'F078_H$	
JTAG_ID	$0018'B083_H$	---	marking EES-AA or ES-AA
	$1018'B083_H$	---	marking AA, AB

3.1 Memory Subsystem and Organization

The memory space of the XE164xN is configured in the von Neumann architecture. In this architecture all internal and external resources, including code memory, data memory, registers and I/O ports, are organized in the same linear address space.

Table 7 XE164xN Memory Map [1)]

Address Area	Start Loc.	End Loc.	Area Size[2)]	Notes
IMB register space	FF'FF00$_H$	FF'FFFF$_H$	256 Bytes	
Reserved	F0'0000$_H$	FF'FEFF$_H$	< 1 Mbyte	Minus IMB registers
Reserved for EPSRAM	E8'4000$_H$	EF'FFFF$_H$	496 Kbytes	Mirrors EPSRAM
Emulated PSRAM	E8'0000$_H$	E8'3FFF$_H$	up to 16 Kbytes	With Flash timing
Reserved for PSRAM	E0'4000$_H$	E7'FFFF$_H$	496 Kbytes	Mirrors PSRAM
PSRAM	E0'0000$_H$	E0'3FFF$_H$	up to 16 Kbytes	Program SRAM
Reserved for Flash	C5'0000$_H$	DF'FFFF$_H$	1,728 Kbytes	
Flash 1	C4'0000$_H$	C4'FFFF$_H$	64 Kbytes	
Flash 0	C0'0000$_H$	C3'FFFF$_H$	256 Kbytes[3)]	Minus res. seg.
External memory area	40'0000$_H$	BF'FFFF$_H$	8 Mbytes	
External IO area[4)]	21'0000$_H$	3F'FFFF$_H$	1,984 Kbytes	
Reserved	20'BC00$_H$	20'FFFF$_H$	17 Kbytes	
USIC0–2 alternate regs.	20'B000$_H$	20'BBFF$_H$	3 Kbytes	Accessed via EBC
MultiCAN alternate regs.	20'8000$_H$	20'AFFF$_H$	12 Kbytes	Accessed via EBC
Reserved	20'5800$_H$	20'7FFF$_H$	10 Kbytes	
USIC0–2 registers	20'4000$_H$	20'57FF$_H$	6 Kbytes	Accessed via EBC
Reserved	20'6800$_H$	20'7FFF$_H$	6 Kbytes	
MultiCAN registers	20'0000$_H$	20'3FFF$_H$	16 Kbytes	Accessed via EBC
External memory area	01'0000$_H$	1F'FFFF$_H$	1984 Kbytes	
SFR area	00'FE00$_H$	00'FFFF$_H$	0.5 Kbytes	
Dualport RAM (DPRAM)	00'F600$_H$	00'FDFF$_H$	2 Kbytes	
Reserved for DPRAM	00'F200$_H$	00'F5FF$_H$	1 Kbytes	
ESFR area	00'F000$_H$	00'F1FF$_H$	0.5 Kbytes	
XSFR area	00'E000$_H$	00'EFFF$_H$	4 Kbytes	
Data SRAM (DSRAM)	00'A000$_H$	00'DFFF$_H$	16 Kbytes	

3.13 Universal Serial Interface Channel Modules (USIC)

The XE164xN features the USIC modules USIC0, USIC1, USIC2. Each module provides two serial communication channels.

The Universal Serial Interface Channel (USIC) module is based on a generic data shift and data storage structure which is identical for all supported serial communication protocols. Each channel supports complete full-duplex operation with a basic data buffer structure (one transmit buffer and two receive buffer stages). In addition, the data handling software can use FIFOs.

The protocol part (generation of shift clock/data/control signals) is independent of the general part and is handled by protocol-specific preprocessors (PPPs).

The USIC's input/output lines are connected to pins by a pin routing unit. The inputs and outputs of each USIC channel can be assigned to different interface pins, providing great flexibility to the application software. All assignments can be made during runtime.

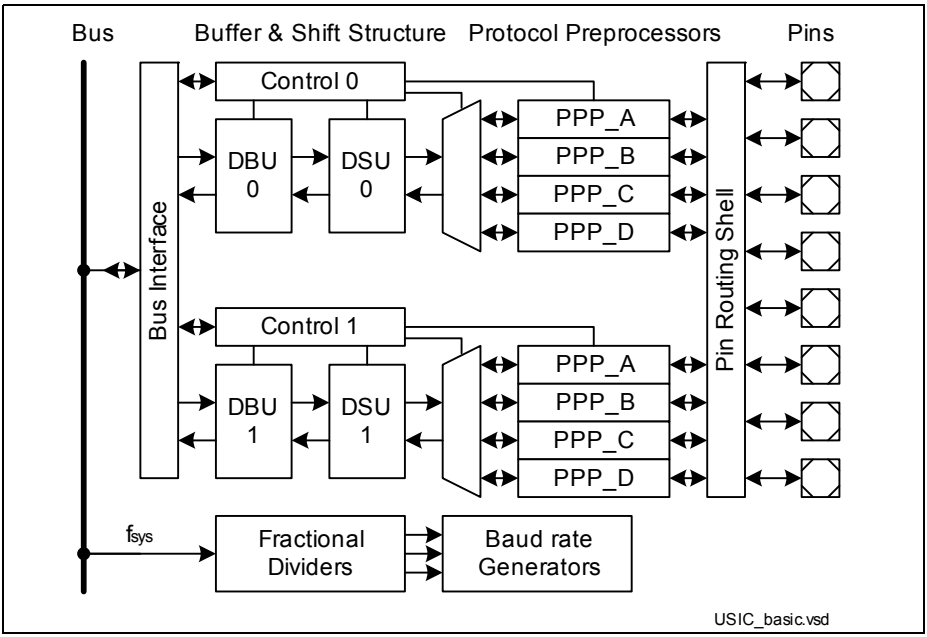


Figure 11 General Structure of a USIC Module

The regular structure of the USIC module brings the following advantages:

- Higher flexibility through configuration with same look-and-feel for data management
- Reduced complexity for low-level drivers serving different protocols
- Wide range of protocols with improved performances (baud rate, buffer handling)

3.18 Parallel Ports

The XE164xN provides up to 76 I/O lines which are organized into 7 input/output ports and 2 input ports. All port lines are bit-addressable, and all input/output lines can be individually (bit-wise) configured via port control registers. This configuration selects the direction (input/output), push/pull or open-drain operation, activation of pull devices, and edge characteristics (shape) and driver characteristics (output current) of the port drivers. The I/O ports are true bidirectional ports which are switched to high impedance state when configured as inputs. During the internal reset, all port pins are configured as inputs without pull devices active.

All port lines have alternate input or output functions associated with them. These alternate functions can be programmed to be assigned to various port pins to support the best utilization for a given application. For this reason, certain functions appear several times in **Table 9**.

All port lines that are not used for alternate functions may be used as general purpose I/O lines.

Table 9 Summary of the XE164xN's Ports

Port	Width	I/O	Connected Modules
P0	8	I/O	EBC (A7...A0), CCU6, USIC, CAN
P1	8	I/O	EBC (A15...A8), CCU6, USIC
P2	14	I/O	EBC (READY, $\overline{\text{BHE}}$, A23...A16, AD15...AD13, D15...D13), CAN, CC2, GPT12E, USIC, DAP/JTAG
P4	4	I/O	EBC ($\overline{\text{CS3}}$...$\overline{\text{CS0}}$), CC2, CAN, GPT12E, USIC
P5	11	I	Analog Inputs, CCU6, DAP/JTAG, GPT12E, CAN
P6	3	I/O	ADC, CAN, GPT12E
P7	5	I/O	CAN, GPT12E, SCU, DAP/JTAG, CCU6, ADC, USIC
P10	16	I/O	EBC (ALE, $\overline{\text{RD}}$, $\overline{\text{WR}}$, AD12...AD0, D12...D0), CCU6, USIC, DAP/JTAG, CAN
P15	5	I	Analog Inputs, GPT12E

3.19 Instruction Set Summary

Table 10 lists the instructions of the XE164xN.
The addressing modes that can be used with a specific instruction, the function of the instructions, parameters for conditional execution of instructions, and the opcodes for each instruction can be found in the **"Instruction Set Manual"**.

This document also provides a detailed description of each instruction.

Table 10 Instruction Set Summary

Mnemonic	Description	Bytes
ADD(B)	Add word (byte) operands	2 / 4
ADDC(B)	Add word (byte) operands with Carry	2 / 4
SUB(B)	Subtract word (byte) operands	2 / 4
SUBC(B)	Subtract word (byte) operands with Carry	2 / 4
MUL(U)	(Un)Signed multiply direct GPR by direct GPR (16- × 16-bit)	2
DIV(U)	(Un)Signed divide register MDL by direct GPR (16-/16-bit)	2
DIVL(U)	(Un)Signed long divide reg. MD by direct GPR (32-/16-bit)	2
CPL(B)	Complement direct word (byte) GPR	2
NEG(B)	Negate direct word (byte) GPR	2
AND(B)	Bitwise AND, (word/byte operands)	2 / 4
OR(B)	Bitwise OR, (word/byte operands)	2 / 4
XOR(B)	Bitwise exclusive OR, (word/byte operands)	2 / 4
BCLR/BSET	Clear/Set direct bit	2
BMOV(N)	Move (negated) direct bit to direct bit	4
BAND/BOR/BXOR	AND/OR/XOR direct bit with direct bit	4
BCMP	Compare direct bit to direct bit	4
BFLDH/BFLDL	Bitwise modify masked high/low byte of bit-addressable direct word memory with immediate data	4
CMP(B)	Compare word (byte) operands	2 / 4
CMPD1/2	Compare word data to GPR and decrement GPR by 1/2	2 / 4
CMPI1/2	Compare word data to GPR and increment GPR by 1/2	2 / 4
PRIOR	Determine number of shift cycles to normalize direct word GPR and store result in direct word GPR	2
SHL/SHR	Shift left/right direct word GPR	2

Table 10 Instruction Set Summary (cont'd)

Mnemonic	Description	Bytes
ROL/ROR	Rotate left/right direct word GPR	2
ASHR	Arithmetic (sign bit) shift right direct word GPR	2
MOV(B)	Move word (byte) data	2 / 4
MOVBS/Z	Move byte operand to word op. with sign/zero extension	2 / 4
JMPA/I/R	Jump absolute/indirect/relative if condition is met	4
JMPS	Jump absolute to a code segment	4
JB(C)	Jump relative if direct bit is set (and clear bit)	4
JNB(S)	Jump relative if direct bit is not set (and set bit)	4
CALLA/I/R	Call absolute/indirect/relative subroutine if condition is met	4
CALLS	Call absolute subroutine in any code segment	4
PCALL	Push direct word register onto system stack and call absolute subroutine	4
TRAP	Call interrupt service routine via immediate trap number	2
PUSH/POP	Push/pop direct word register onto/from system stack	2
SCXT	Push direct word register onto system stack and update register with word operand	4
RET(P)	Return from intra-segment subroutine (and pop direct word register from system stack)	2
RETS	Return from inter-segment subroutine	2
RETI	Return from interrupt service subroutine	2
SBRK	Software Break	2
SRST	Software Reset	4
IDLE	Enter Idle Mode	4
PWRDN	Unused instruction[1)]	4
SRVWDT	Service Watchdog Timer	4
DISWDT/ENWDT	Disable/Enable Watchdog Timer	4
EINIT	End-of-Initialization Register Lock	4
ATOMIC	Begin ATOMIC sequence	2
EXTR	Begin EXTended Register sequence	2
EXTP(R)	Begin EXTended Page (and Register) sequence	2 / 4
EXTS(R)	Begin EXTended Segment (and Register) sequence	2 / 4

Table 10 Instruction Set Summary (cont'd)

Mnemonic	Description	Bytes
NOP	Null operation	2
CoMUL/CoMAC	Multiply (and accumulate)	4
CoADD/CoSUB	Add/Subtract	4
Co(A)SHR	(Arithmetic) Shift right	4
CoSHL	Shift left	4
CoLOAD/STORE	Load accumulator/Store MAC register	4
CoCMP	Compare	4
CoMAX/MIN	Maximum/Minimum	4
CoABS/CoRND	Absolute value/Round accumulator	4
CoMOV	Data move	4
CoNEG/NOP	Negate accumulator/Null operation	4

1) The Enter Power Down Mode instruction is not used in the XE164xN, due to the enhanced power control scheme. PWRDN will be correctly decoded, but will trigger no action.

Table 12 Operating Conditions (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Overload current coupling factor for digital I/O pins	K_{OVD} CC	–	1.0 x 10^{-2}	3.0 x 10^{-2}	-	I_{OV}< 0 mA; not subject to production test
		–	1.0 x 10^{-4}	5.0 x 10^{-3}	-	I_{OV}> 0 mA; not subject to production test
Absolute sum of overload currents	$\Sigma\|I_{OV}\|$ SR	–	–	50	mA	not subject to production test
Digital core supply voltage for domain M[8)]	V_{DDIM} CC	–	1.5	–		
Digital core supply voltage for domain 1[8)]	V_{DDI1} CC	–	1.5	–		
Digital supply voltage for IO pads and voltage regulators	V_{DDP} SR	3.0	–	5.5	V	
Digital ground voltage	V_{SS} SR	–	0	–	V	

1) To ensure the stability of the voltage regulators the EVRs must be buffered with ceramic capacitors. Separate buffer capacitors with the recomended values shall be connected as close as possible to each V_{DDIM} and V_{DDI1} pin to keep the resistance of the board tracks below 2 Ohm. Connect all V_{DDI1} pins together. The minimum capacitance value is required for proper operation under all conditions (e.g. temperature). Higher values slightly increase the startup time.

2) Use one Capacitor for each pin.

3) This is the reference load. For bigger capacitive loads, use the derating factors listed in the pad properties section.

4) The timing is valid for pin drivers operating in default current mode (selected after reset). Reducing the output current may lead to increased delays or reduced driving capability (C_L).

5) The operating frequency range may be reduced for specific device types. This is indicated in the device designation (...FxxL). 80 MHz devices are marked ...F80L.

6) Overload conditions occur if the standard operating conditions are exceeded, i.e. the voltage on any pin exceeds the specified range: $V_{OV} > V_{IHmax}$ ($I_{OV} > 0$) or $V_{OV} < V_{ILmin}$ (($I_{OV} < 0$). The absolute sum of input overload currents on all pins may not exceed 50 mA. The supply voltages must remain within the specified limits. Proper operation under overload conditions depends on the application. Overload conditions must not occur on pin XTAL1 (powered by V_{DDIM}).

4.3 DC Parameters

These parameters are static or average values that may be exceeded during switching transitions (e.g. output current).

The XE164xN can operate within a wide supply voltage range from 3.0 V to 5.5 V. However, during operation this supply voltage must remain within 10 percent of the selected nominal supply voltage. It cannot vary across the full operating voltage range.

Because of the supply voltage restriction and because electrical behavior depends on the supply voltage, the parameters are specified separately for the upper and the lower voltage range.

During operation, the supply voltages may only change with a maximum speed of dV/dt < 1 V/ms.

Leakage current is strongly dependent on the operating temperature and the voltage level at the respective pin. The maximum values in the following tables apply under worst case conditions, i.e. maximum temperature and an input level equal to the supply voltage.
The value for the leakage current in an application can be determined by using the respective leakage derating formula (see tables) with values from that application.

The pads of the XE164xN are designed to operate in various driver modes. The DC parameter specifications refer to the pad current limits specified in **Section 4.7.4**.

Table 15 DC Characteristics for Upper Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output High voltage[7]	V_{OH} CC	V_{DDP} - 1.0	–	–	V	$I_{OH} \geq I_{OHmax}$
		V_{DDP} - 0.4	–	–	V	$I_{OH} \geq I_{OHnom}$ [8]
Output Low Voltage[7]	V_{OL} CC	–	–	0.4	V	$I_{OL} \leq I_{OLnom}$ [8]
		–	–	1.0	V	$I_{OL} \leq I_{OLmax}$

1) Because each double bond pin is connected to two pads (standard pad and high-speed pad), it has twice the normal value. For a list of affected pins refer to the pin definitions table in chapter 2.

2) Not subject to production test - verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.

3) If the input voltage exceeds the respective supply voltage due to ground bouncing ($V_{IN} < V_{SS}$) or supply ripple ($V_{IN} > V_{DDP}$), a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor K_{OV}.

4) The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T_J = junction temperature [°C]): $I_{OZ} = 0.05 \times e^{(1.5 + 0.028 \times TJ>)}$ [µA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 µA. Leakage derating depending on voltage level (DV = V_{DDP} - V_{PIN} [V]): $I_{OZ} = I_{OZtempmax}$ - (1.6 x DV) (µA]. This voltage derating formula is an approximation which applies for maximum temperature.

5) Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device.

6) Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level.

7) The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.

8) As a rule, with decreasing output current the output levels approach the respective supply level (V_{OL}->V_{SS}, V_{OH}->V_{DDP}). However, only the levels for nominal output currents are verified.

4.3.2 DC Parameters for Lower Voltage Area

Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the overload current I_{OV}.

Note: Operating Conditions apply.

Table 16 is valid under the following conditions: $V_{DDP} \geq$ 3.0 V; V_{DDP}typ. 3.3 V; $V_{DDP} \leq$ 4.5 V

Table 16 DC Characteristics for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Pin capacitance (digital inputs/outputs). To be doubled for double bond pins.[1]	C_{IO} CC	–	–	10	pF	not subject to production test
Input Hysteresis[2]	HYS CC	0.07 x V_{DDP}	–	–	V	R_S= 0 Ohm
Absolute input leakage current on pins of analog ports[3]	$\|I_{OZ1}\|$ CC	–	10	200	nA	$V_{IN} > V_{SS}$; $V_{IN} < V_{DDP}$
Absolute input leakage current for all other pins. To be doubled for double bond pins.[3][1][4]	$\|I_{OZ2}\|$ CC	–	0.2	2.5	µA	$T_J \leq$ 110 °C; $V_{IN} > V_{SS}$; $V_{IN} < V_{DDP}$
		–	0.2	8	µA	$T_J \leq$ 150 °C; $V_{IN} > V_{SS}$; $V_{IN} < V_{DDP}$
Pull Level Force Current[5]	$\|I_{PLF}\|$ SR	150	–	–	µA	$V_{IN} \geq V_{IHmin}$*(pull down)* ; $V_{IN} \leq V_{ILmax}$*(pull up)*
Pull Level Keep Current[6]	$\|I_{PLK}\|$ SR	–	–	10	µA	$V_{IN} \geq V_{IHmin}$*(pull up)* ; $V_{IN} \leq V_{ILmax}$*(pull down)*
Input high voltage (all except XTAL1)	V_{IH} SR	0.7 x V_{DDP}	–	V_{DDP} + 0.3	V	
Input low voltage (all except XTAL1)	V_{IL} SR	-0.3	–	0.3 x V_{DDP}	V	

Direct Drive

When direct drive operation is selected (SYSCON0.CLKSEL = 11_B), the system clock is derived directly from the input clock signal CLKIN1:

$f_{SYS} = f_{IN}$.

The frequency of f_{SYS} is the same as the frequency of f_{IN}. In this case the high and low times of f_{SYS} are determined by the duty cycle of the input clock f_{IN}.

Selecting Bypass Operation from the XTAL1[1)] input and using a divider factor of 1 results in a similar configuration.

Prescaler Operation

When prescaler operation is selected (SYSCON0.CLKSEL = 10_B, PLLCON0.VCOBY = 1_B), the system clock is derived either from the crystal oscillator (input clock signal XTAL1) or from the internal clock source through the output prescaler K1 (= K1DIV+1):

$f_{SYS} = f_{OSC} / K1$.

If a divider factor of 1 is selected, the frequency of f_{SYS} equals the frequency of f_{OSC}. In this case the high and low times of f_{SYS} are determined by the duty cycle of the input clock f_{OSC} (external or internal).

The lowest system clock frequency results from selecting the maximum value for the divider factor K1:

$f_{SYS} = f_{OSC} / 1024$.

4.7.2.1 Phase Locked Loop (PLL)

When PLL operation is selected (SYSCON0.CLKSEL = 10_B, PLLCON0.VCOBY = 0_B), the on-chip phase locked loop is enabled and provides the system clock. The PLL multiplies the input frequency by the factor **F** ($f_{SYS} = f_{IN} \times$ **F**).
F is calculated from the input divider P (= PDIV+1), the multiplication factor N (= NDIV+1), and the output divider K2 (= K2DIV+1):
(**F** = N / (P $\times$ K2)).

The input clock can be derived either from an external source at XTAL1 or from the on-chip clock source.

The PLL circuit synchronizes the system clock to the input clock. This synchronization is performed smoothly so that the system clock frequency does not change abruptly.

Adjustment to the input clock continuously changes the frequency of f_{SYS} so that it is locked to f_{IN}. The slight variation causes a jitter of f_{SYS} which in turn affects the duration of individual TCSs.

1) Voltages on XTAL1 must comply to the core supply voltage V_{DDIM}.

Table 32 External Bus Timing for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output valid delay for $\overline{RD}$, $\overline{WR}$(L/$\overline{H}$)	t_{10} CC	–	11	20	ns	
Output valid delay for $\overline{BHE}$, ALE	t_{11} CC	–	10	21	ns	
Address output valid delay for A23 ... A0	t_{12} CC	–	11	22	ns	
Address output valid delay for AD15 ... AD0 (MUX mode)	t_{13} CC	–	10	22	ns	
Output valid delay for $\overline{CS}$	t_{14} CC	–	10	13	ns	
Data output valid delay for AD15 ... AD0 (write data, MUX mode)	t_{15} CC	–	10	22	ns	
Data output valid delay for D15 ... D0 (write data, DEMUX mode)	t_{16} CC	–	10	22	ns	
Output hold time for $\overline{RD}$, $\overline{WR}$(L/$\overline{H}$)	t_{20} CC	-2	8	10	ns	
Output hold time for $\overline{BHE}$, ALE	t_{21} CC	-2	8	10	ns	
Address output hold time for AD15 ... AD0	t_{23} CC	-3	8	10	ns	
Output hold time for $\overline{CS}$	t_{24} CC	-3	8	11	ns	
Data output hold time for D15 ... D0 and AD15 ... AD0	t_{25} CC	-3	8	10	ns	
Input setup time for READY, D15 ... D0, AD15 ... AD0	t_{30} SR	29	17	–	ns	
Input hold time READY, D15 ... D0, AD15 ... AD0[1)]	t_{31} SR	0	-9	–	ns	

1) Read data are latched with the same internal clock edge that triggers the address change and the rising edge of RD. Address changes before the end of RD have no impact on (demultiplexed) read cycles. Read data can change after the rising edge of RD.

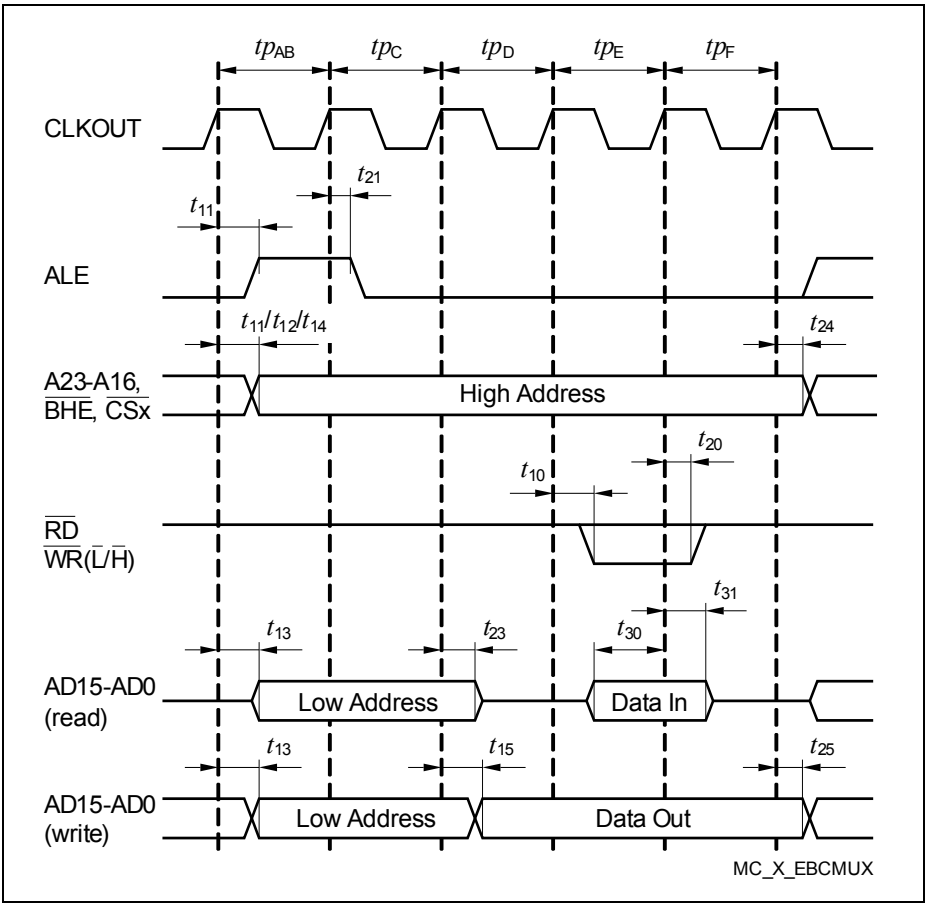


Figure 23 Multiplexed Bus Cycle

Note: If the READY input is sampled inactive at the indicated sampling point (“Not Rdy”) a READY-controlled waitstate is inserted (tpRDY),
sampling the READY input active at the indicated sampling point (“Ready”) terminates the currently running bus cycle.
Note the different sampling points for synchronous and asynchronous READY.
This example uses one mandatory waitstate (see tpE) before the READY input value is used.

5.3 Quality Declarations

The operation lifetime of the XE164xN depends on the operating temperature. The life time decreases with increasing temperature as shown in **Table 43**.

Table 42 Quality Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Operation lifetime	t_{OP} CC	–	–	20	a	See **Table 43**
ESD susceptibility according to Human Body Model (HBM)	V_{HBM} SR	–	–	2 000	V	EIA/JESD22-A114-B
Moisture sensitivity level	MSL CC	–	–	3	–	JEDEC J-STD-020C

Table 43 Lifetime dependency from Temperature

Operating Time	Operating Temperature
20 a	$T_J \leq 110°C$
95 500 h	$T_J = 120°C$
68 500 h	$T_J = 125°C$
49 500 h	$T_J = 130°C$
26 400 h	$T_J = 140°C$
14 500 h	$T_J = 150°C$